

Product Overview

MBRA210LT3: Schottky Power Rectifier, Surface Mount, 2.0 A, 10 V

For complete documentation, see the data sheet.

...employing the Schottky Barrier principle in a metal-to-silicon power rectifier. Features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency switching power supplies; free wheeling diodes and polarity protection diodes. Typical applications are ac/dc and dc-dc converters, reverse battery protection, and "O-ring" of multiple supply voltages and any other application where performance and size are critical.

Features

- Ultra Low VF
- 1st in the Market Place with a 10 VR Schottky Rectifier
- Compact Package with J-Bend Leads Ideal for Automated Handling
- Highly Stable Oxide Passivated Junction
- Guardring for Over-Voltage Protection
- Optimized for Low Forward Current
- Mechanical Characteristics: Case: Molded Epoxy
- Epoxy Meets UL94, VO at 1/8"
- Weight: 70 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable

For more features, see the data sheet

Part Electrical Specifications

Product	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (μ A)	$I_{O(rec)}$ Max (A)	I_{FSM} Max (A)	t_r Max (ns)	C_j Max (pF)	Package Type
MBRA210LT3G	Pb-free	Active	Single	10	0.35	700	2	230	-	-	SMA-2
	Halide free										
NRVBA210LT3G	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	10	0.35	700	2	230	-	-	SMA-2

For more information please contact your local sales support at www.onsemi.com.

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